

To our customers,

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## Old Company Name in Catalogs and Other Documents

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April 1<sup>st</sup>, 2010  
Renesas Electronics Corporation

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Not recommended  
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## 3SK295

### Silicon N-Channel Dual Gate MOS FET

REJ03G0814-0300  
(Previous ADE-208-387A)  
Rev.3.00  
Aug. 10, 2005

#### Application

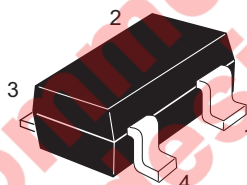
- UHF RF amplifier

#### Features

- Low noise figure.  
NF = 2.0 dB typ. at f = 900 MHz
- Capable of low voltage operation

#### Outline

RENESAS Package code: PLSP0004ZA-A  
(Package name: MPAK-4)



1. Source
2. Gate1
3. Gate2
4. Drain

Note: Marking is "ZQ—"

#### Attention:

This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.

## Absolute Maximum Ratings

(Ta = 25°C)

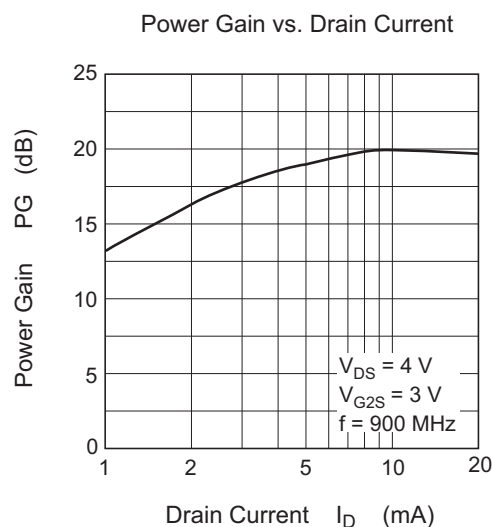
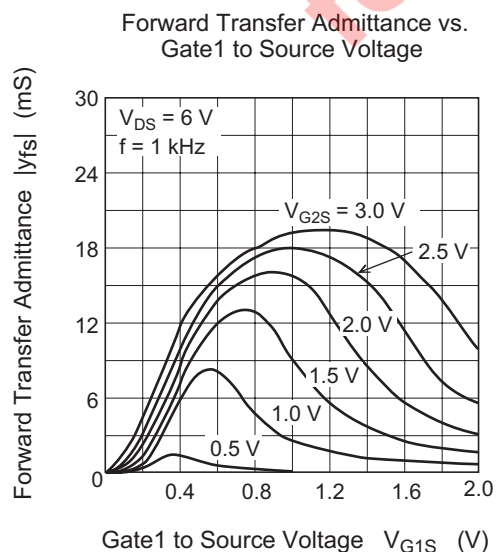
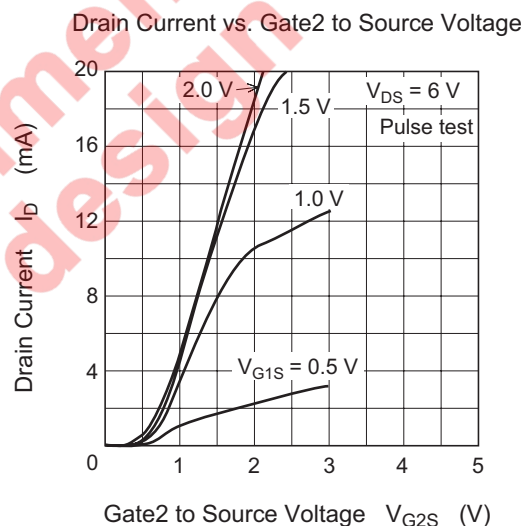
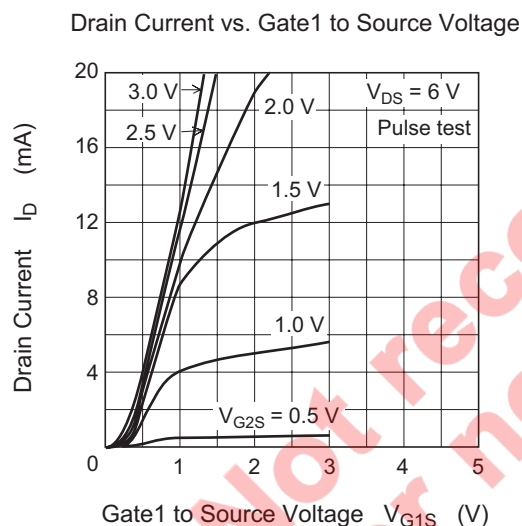
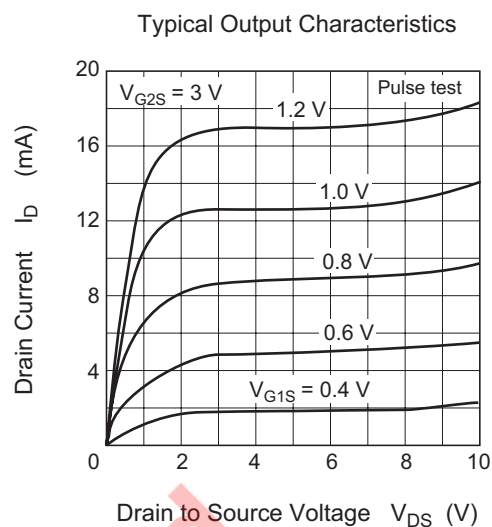
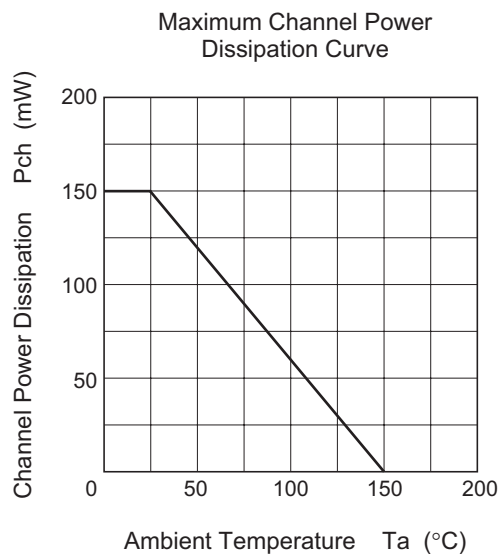
| Item                      | Symbol    | Ratings     | Unit |
|---------------------------|-----------|-------------|------|
| Drain to source voltage   | $V_{DS}$  | 12          | V    |
| Gate 1 to source voltage  | $V_{G1S}$ | $\pm 8$     | V    |
| Gate 2 to source voltage  | $V_{G2S}$ | $\pm 8$     | V    |
| Drain current             | $I_D$     | 25          | mA   |
| Channel power dissipation | Pch       | 150         | mW   |
| Channel temperature       | Tch       | 150         | °C   |
| Storage temperature       | Tstg      | -55 to +150 | °C   |

## Electrical Characteristics

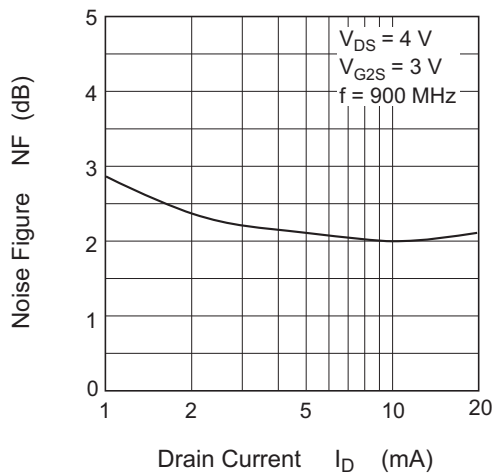
(Ta = 25°C)

| Item                               | Symbol         | Min     | Typ  | Max       | Unit | Test conditions                                                     |
|------------------------------------|----------------|---------|------|-----------|------|---------------------------------------------------------------------|
| Drain to source breakdown voltage  | $V_{(BR)DSX}$  | 12      | —    | —         | V    | $I_D = 200 \mu A$ , $V_{G1S} = -3 V$ ,<br>$V_{G2S} = -3 V$          |
| Gate 1 to source breakdown voltage | $V_{(BR)G1SS}$ | $\pm 8$ | —    | —         | V    | $I_{G1} = \pm 10 \mu A$ , $V_{G2S} = V_{DS} = 0$                    |
| Gate 2 to source breakdown voltage | $V_{(BR)G2SS}$ | $\pm 8$ | —    | —         | V    | $I_{G2} = \pm 10 \mu A$ , $V_{G1S} = V_{DS} = 0$                    |
| Gate 1 cutoff current              | $I_{G1SS}$     | —       | —    | $\pm 100$ | nA   | $V_{G1S} = \pm 6 V$ , $V_{G2S} = V_{DS} = 0$                        |
| Gate 2 cutoff current              | $I_{G2SS}$     | —       | —    | $\pm 100$ | nA   | $V_{G2S} = \pm 6 V$ , $V_{G1S} = V_{DS} = 0$                        |
| Drain current                      | $I_{DS(on)}$   | 0.5     | —    | 10        | mA   | $V_{DS} = 6 V$ , $V_{G1S} = 0.5 V$ ,<br>$V_{G2S} = 3 V$             |
| Gate 1 to source cutoff voltage    | $V_{G1S(off)}$ | -0.5    | —    | +0.5      | V    | $V_{DS} = 10 V$ , $V_{G2S} = 3 V$ ,<br>$I_D = 100 \mu A$            |
| Gate 2 to source cutoff voltage    | $V_{G2S(off)}$ | 0       | —    | +1.0      | V    | $V_{DS} = 10 V$ , $V_{G1S} = 3 V$ ,<br>$I_D = 100 \mu A$            |
| Forward transfer admittance        | $ y_{fs} $     | 16      | 20.8 | —         | mS   | $V_{DS} = 6 V$ , $V_{G2S} = 3 V$ ,<br>$I_D = 10 mA$ , $f = 1 kHz$   |
| Input capacitance                  | $C_{iss}$      | 1.2     | 1.5  | 2.2       | pF   | $V_{DS} = 6 V$ , $V_{G2S} = 3 V$ ,<br>$I_D = 10 mA$ , $f = 1 MHz$   |
| Output capacitance                 | $C_{oss}$      | 0.6     | 0.9  | 1.2       | pF   |                                                                     |
| Reverse transfer capacitance       | $C_{rss}$      | —       | 0.01 | 0.03      | pF   |                                                                     |
| Power gain                         | PG             | 16      | 19.5 | —         | dB   | $V_{DS} = 4 V$ , $V_{G2S} = 3 V$ ,<br>$I_D = 10 mA$ , $f = 900 MHz$ |
| Noise figure                       | NF             | —       | 2.0  | 3         | dB   |                                                                     |

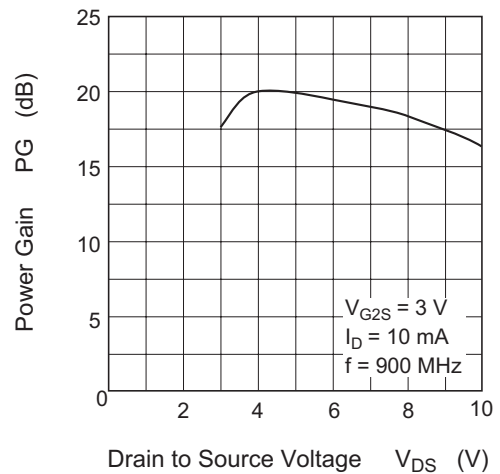
## Main Characteristics



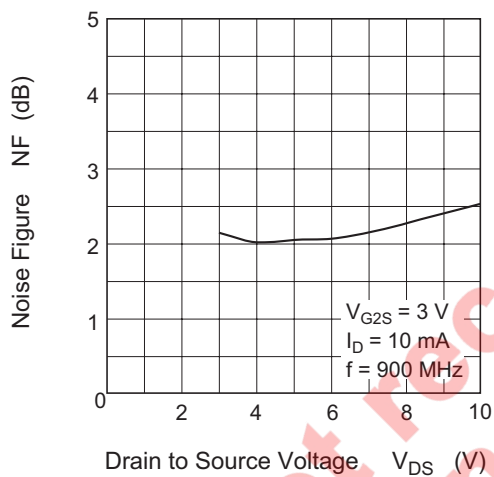
Noise Figure vs. Drain Current



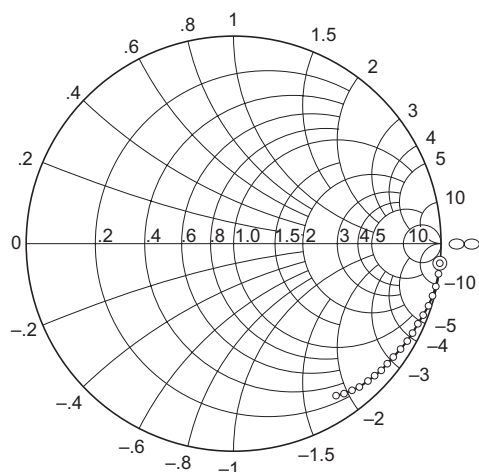
Power Gain vs. Drain to Source Voltage



Noise Figure vs. Drain to Source Voltage



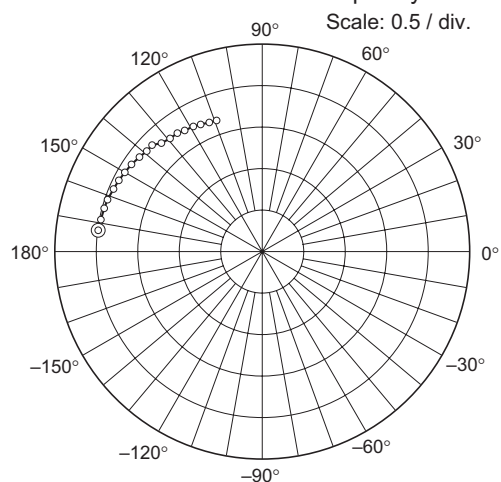
S11 Parameter vs. Frequency



Condition:  $V_{DS} = 4\text{ V}$ ,  $V_{GS} = 3\text{ V}$   
 $I_D = 10\text{ mA}$ ,  $Z_0 = 50\ \Omega$   
 100 to 1000 MHz (50 MHz step)



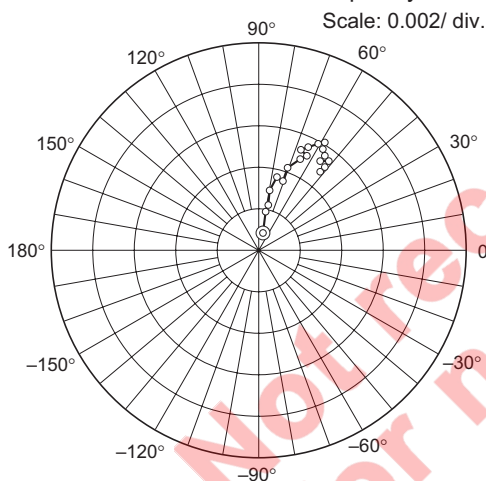
S21 Parameter vs. Frequency



Condition:  $V_{DS} = 4\text{ V}$ ,  $V_{GS} = 3\text{ V}$   
 $I_D = 10\text{ mA}$ ,  $Z_0 = 50\ \Omega$   
 100 to 1000 MHz (50 MHz step)



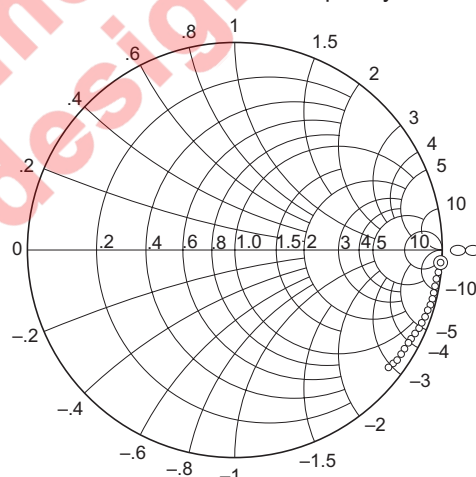
S12 Parameter vs. Frequency



Condition:  $V_{DS} = 4\text{ V}$ ,  $V_{GS} = 3\text{ V}$   
 $I_D = 10\text{ mA}$ ,  $Z_0 = 50\ \Omega$   
 100 to 1000 MHz (50 MHz step)



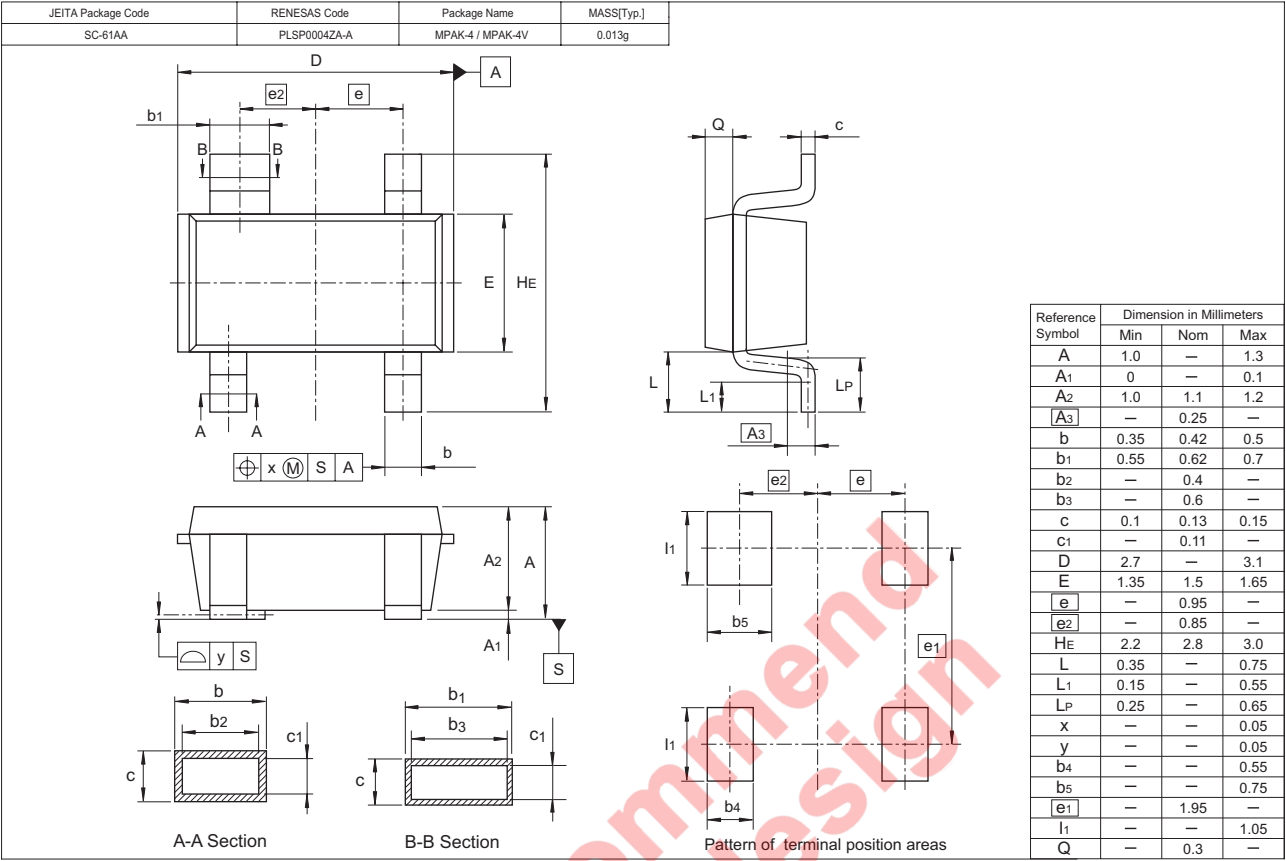
S22 Parameter vs. Frequency



Condition:  $V_{DS} = 4\text{ V}$ ,  $V_{GS} = 3\text{ V}$   
 $I_D = 10\text{ mA}$ ,  $Z_0 = 50\ \Omega$   
 100 to 1000 MHz (50 MHz step)



Package Dimensions



Ordering Information

| Part Name     | Quantity | Shipping Container               |
|---------------|----------|----------------------------------|
| 3SK295ZQ-TL-E | 3000     | φ178 mm Reel, 8 mm Emboss Taping |

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